

IN THE ABSTRACT OF THE DISCLOSURE

Please delete the abstract sheet in its entirety and insert therefor:

--ABSTRACT OF THE DISCLOSURE

AB A process for fabricating a structure including a carrier substrate and a layer of semiconductor material on one surface of the carrier substrate. The process a) forms a layer of semiconductor material on one surface of a first substrate, b) forms a cleavage zone in the first substrate, which delimits a superficial layer, c) transfers the first substrate, with the layer of semiconductor material, onto the carrier substrate, d) provides energy to cause cleavage of the first substrate along the cleavage zone, and e) removes said superficial layer to uncover the layer of semiconductor material.--

REMARKS

Favorable consideration of this application, as presently amended, is respectfully requested.

The present preliminary amendment is submitted to place the above-identified application in more proper format under United States practice. By the present preliminary amendment the specification has been amended to include suggested headings. The claims have been amended to no longer recite any reference numerals or multiple dependencies. The subject matter of the cancelled multiple dependencies is also now submitted in new dependent Claim 13. A new abstract believed to be in more proper format under United States practice is also submitted herein.

The present application is believed to be in condition for a full and through examination on the merits. An early and favorable consideration of the present application is hereby respectfully requested.

Respectfully submitted,

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